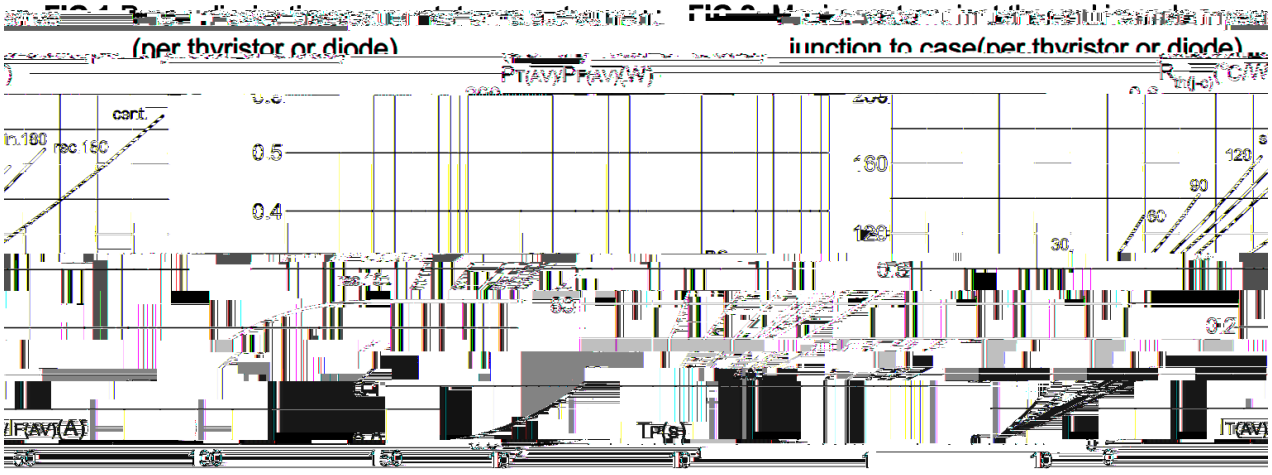
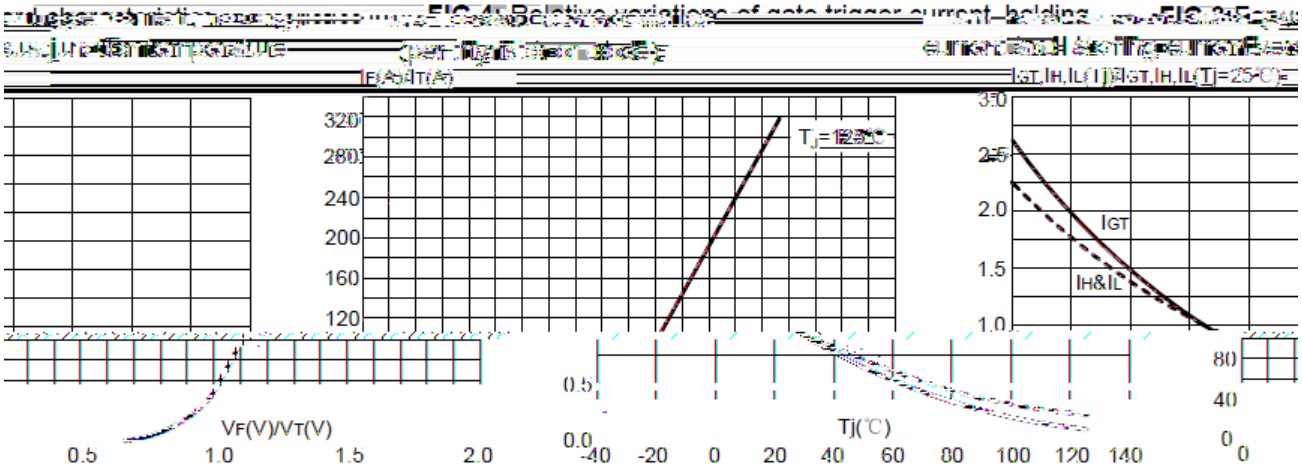
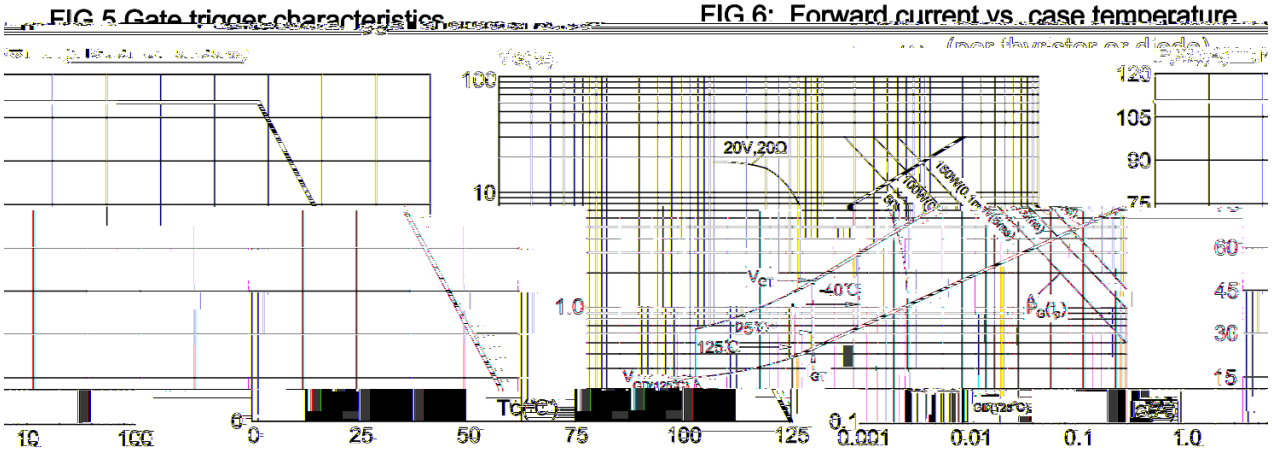
	℃					
	℃					
	℃					
	℃					
	℃					
	℃					
	℃					
	℃					

			±		


(per thyristor or diode)
junction to case(per thyristor or diode)
PT(AV)/PF(AV)(W)
cont.
180
rec 180
0.5
0.4
120
90
60
30
IF(AV)(A)
TP(s)
IT(AV)


IGT,IH,IL(T)/IGT,IH,IL(Tj=25℃)
320
280
240
200
160
120
Tj=125℃
3.0
2.5
2.0
1.5
1.0
IGT
IH&IL
0.5
0.0
80
40
0
VF(V)/VT(V)
0.5
1.0
1.5
2.0
Tj(℃)
-40
-20
0
20
40
60
80
100
120
140


100
10
1.0
0.1
20V,20Ω
VGT
-40℃
125℃
IGT
VGD
IGD
PG(AV)
120
105
90
75
60
45
30
15
0
25
50
75
100
125
0.001
0.01
0.1
1.0